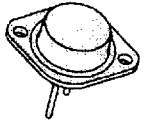


NEW ENGLAND SEMICONDUCTOR

**BIPOLAR
NPN TRANSISTOR
TO-3**

| PACKAGE | DEVICE TYPE | V _{CEO} (sus) VOLTS | I _C (max) AMPS | h _{FE} @ I _C / V _{CE} (min/max @ A/V) | V _{CE(sat)} @ I _C /I _B (V @ A/A) | P _D * WATTS | f _T (MHZ) |
|--|-------------|------------------------------------|---------------------------------|--|---|---------------------------|-------------------------|
| NPN TO-3  | 2N6032^ | 90 | 50 | 10-50@50/2.6 | 1.3@50/5 | 140 | 30 ^t |
| | 2N6033^ | 120 | 40 | 10-50@40/2 | 1@40/4 | 140 | 30 ^t |
| | 2N6274^ | 100 | 50 | 30-120@20/4 | 1.2@20/2 | 250 | 30 |
| | 2N6275 | 120 | 50 | 30-120@20/4 | 1.2@20/2 | 250 | 30 |
| | 2N6276 | 140 | 50 | 30-120@20/4 | 1.2@20/2 | 250 | 30 |
| | 2N6277^ | 150 | 50 | 30-120@20/4 | 1.2@20/2 | 250 | 30 |
| | 2N6322 | 200 | 30 | 40-150@5/5 | 1.5@20/2 | 350 | 10 |
| | 2N6323 | 300 | 30 | 30-150@5/5 | 1.5@20/2 | 350 | 10 |
| | 2N6326 | 60 | 30 | 6-30@30/4 | 1.5@15/2 | 200 | 3 |
| | 2N6327 | 80 | 30 | 6-30@30/4 | 1.5@15/4 | 200 | 3 |
| | 2N6338^ | 100 | 25 | 30-120@10/2 | 1@10/1 | 200 | 40 |
| | 2N6340 | 140 | 25 | 30-120@10/1 | 1@10/1 | 200 | 40 |
| | 2N6341^ | 150 | 25 | 30-120@10/1 | 1@10/1 | 200 | 40 |
| | 2N6354 | 120 | 10 | 10-100@10/2 | 1@10/1 | 140 | 60 ^t |
| | 2N6510 | 200 | 7 | 10-50@3/3 | 1.5@3/6 | 120 | 3 |
| | 2N6511 | 250 | 7 | 10-50@4/3 | 1.5@4/8 | 120 | 3 |
| | 2N6512 | 300 | 7 | 10-50@4/3 | 1.5@4/8 | 120 | 3 |
| | 2N6676^ | 350 | 15 | >8@15/3 | 1@15/3 | 175 | 15 |
| | 2N6677 | 350 | 15 | >8@15/3 | 1.5@15/3 | 175 | 15 |
| | 2N6678^ | 400 | 15 | >8@15/3 | 1.5@15/3 | 175 | 15 |
| 2N6686 | 160 | 25 | 25-100@10/2 | 1.5@25/2.5 | 200 | 20 | |
| 2N6687 | 180 | 25 | 25-100@10/2 | 1.5@25/2.5 | 200 | 20 | |
| 2N6688 | 200 | 25 | 20-80@10/2 | 1.5@20/2 | 200 | 20 | |

* T_C = 25°C

^h V_{CER}

^t Typical

^Available in JAN, JANTX, JANTXV